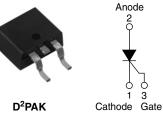


Vishay High Power Products

Surface Mountable Phase Control SCR, 16 A



PRODUCT SUMMARY						
V_T at 16 A	< 1.25 V					
I _{TSM}	300 A					
V _{RRM}	800 to 1600 V					

DESCRIPTION/FEATURES

The 25TTS...S High Voltage Series of silicon controlled rectifiers are specifically designed for medium power switching and phase control applications. The glass passivation technology used has reliable operation up to 125 °C junction temperature.

Typical applications are in input rectification (soft start) and these products are designed to be used with Vishay HPP input diodes, switches and output rectifiers which are available in identical package outlines.

This product has been designed and qualified for industrial level.

OUTPUT CURRENT IN TYPICAL APPLICATIONS								
APPLICATIONS SINGLE-PHASE BRIDGE THREE-PHASE BRIDGE UNITS								
NEMA FR-4 or G10 glass fabric-based epoxy with 4 oz. (140 $\mu m)$ copper	3.5	5.5						
Aluminum IMS, R _{thCA} = 15 °C/W	8.5	13.5	A					
Aluminum IMS with heatsink, $R_{thCA} = 5 \text{ °C/W}$	16.5	25.0						

Note

• $T_A = 55 \text{ °C}, T_J = 125 \text{ °C}, \text{ footprint } 300 \text{ mm}^2$

MAJOR RATINGS AND CHARACTERISTICS							
PARAMETER	TEST CONDITIONS	VALUES	UNITS				
I _{T(AV)}	Sinusoidal waveform	16	А				
I _{RMS}		25	A				
V _{RRM} /V _{DRM}		800 to 1600	V				
I _{TSM}		300	А				
V _T	16 A, T _J = 25 °C	1.25	V				
dV/dt		500	V/µs				
dl/dt		150	A/µs				
TJ		- 40 to 125	°C				

VOLTAGE RATINGS								
PART NUMBER	V _{RRM} , MAXIMUM PEAK REVERSE VOLTAGE V	V _{DRM} , MAXIMUM PEAK DIRECT VOLTAGE V	I _{RRM} /I _{DRM} , AT 125 °C mA					
25TTS08S	800	800						
25TTS12S	1200	1200	10					
25TTS16S	1600	1600						

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ABSOLUTE MAXIMUM RATINGS							
PARAMETER	SYMBOL TEST CONDITIONS						
PARAMEIER			TYP.	MAX.			
Maximum average on-state current	I _{T(AV)}	$T_{\rm C} = 93 \ ^{\circ}{\rm C}, \ 180^{\circ} \ {\rm conduct}$	uction half sine wave	1	6		
Maximum RMS on-state current	I _{RMS}			2	.5		
Maximum peak, one-cycle,	1	10 ms sine pulse, rated	d V _{RRM} applied	3	00	A	
non-repetitive surge current	I _{TSM}	10 ms sine pulse, no v	oltage reapplied	3	50	1	
Maximum 12t for fusing	l ² t	10 ms sine pulse, rated	d V _{RRM} applied	4	50	A ² s	
Maximum I ² t for fusing	1-1	10 ms sine pulse, no v	oltage reapplied	630		A ² S	
Maximum I ² \sqrt{t} for fusing	l²√t	t = 0.1 to 10 ms, no vol	t = 0.1 to 10 ms, no voltage reapplied				
Maximum on-state voltage drop	V _{TM}	16 A, T _J = 25 °C	16 A, T _J = 25 °C				
On-state slope resistance	r _t	T 105 %			2.0	mΩ	
Threshold voltage	V _{T(TO)}	T _J = 125 °C			.0	V	
		T _J = 25 °C		0	.5		
Maximum reverse and direct leakage current	I _{RM} /I _{DM}	$T_J = 125 \degree C$ $V_R = Rated V_{RRM}/V_{DRM}$		1	0		
Loding ourrest	1	25TTS08, 25TTS12	Anode supply = 6 V,	-	100	mA	
Holding current	IH	25TTS16	resistive load, initial $I_T = 1 A$	100	150		
Maximum latching current	١L	Anode supply = 6 V, resistive load			00		
Maximum rate of rise of off-state voltage	dV/dt				00	V/µs	
Maximum rate of rise of turned-on current	dl/dt				50	A/µs	

TRIGGERING					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Maximum peak gate power	P _{GM}		8.0	w	
Maximum average gate power	$P_{G(AV)}$		2.0	vv	
Maximum peak positive gate current	+ I _{GM}		1.5	А	
Maximum peak negative gate voltage	- V _{GM}		10	V	
Maximum required DC gate current to trigger	I _{GT}	Anode supply = 6 V, resistive load, $T_J = -10 \degree C$	60	mA	
		Anode supply = 6 V, resistive load, $T_J = 25 \ ^{\circ}C$	45		
		Anode supply = 6 V, resistive load, $T_J = 125 \ ^{\circ}C$	20		
		Anode supply = 6 V, resistive load, $T_J = -10 \degree C$	2.5		
Maximum required DC gate voltage to trigger	V _{GT}	Anode supply = 6 V, resistive load, $T_J = 25 \ ^{\circ}C$	2.0	v	
		Anode supply = 6 V, resistive load, $T_J = 125 \ ^{\circ}C$	1.0	v	
Maximum DC gate voltage not to trigger	V_{GD}	$T_{J} = 125 \text{ °C}, V_{DRM} = \text{Rated value}$ $\frac{0.25}{2.0}$			
Maximum DC gate current not to trigger	I _{GD}			mA	

SWITCHING							
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS			
Typical turn-on time	t _{gt}	T _J = 25 °C	0.9				
Typical reverse recovery time	t _{rr}	T _{.1} = 125 °C	4	μs			
Typical turn-off time	t _q	1J = 125 C	110				





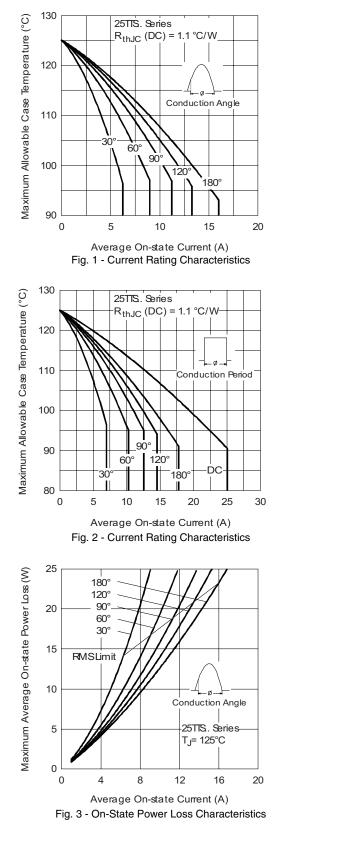
Surface Mountable Phase Vishay High Power Products Control SCR, 16 A

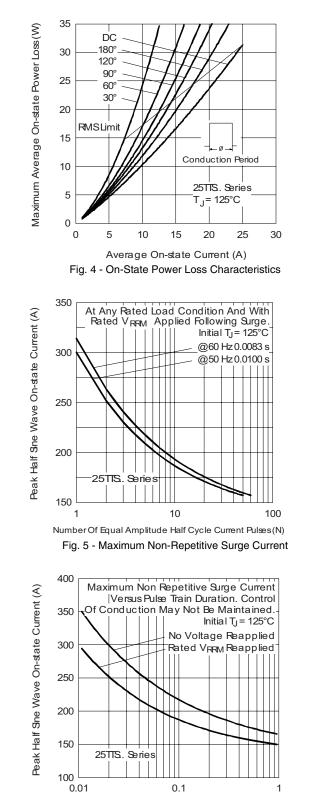
THERMAL AND MECHANICAL SPECIFICATIONS							
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS			
Maximum junction and storage temperature range	T _J , T _{Stg}		- 40 to 125	°C			
Soldering temperature	T _S	For 10 s (1.6 mm from case)	240				
Maximum thermal resistance, junction to case	R _{thJC}	DC operation	1.1	°C/W			
Typical thermal resistance, junction to ambient (PCB mount)	R _{thJA} ⁽¹⁾		40	0/11			
Approximate weight			2	g			
Approximate weight			0.07	oz.			
			25TTS0	8S			
Marking device		Case style D ² PAK (SMD-220)	25TTS1	2S			
			25TTS1	6S			

Note

⁽¹⁾ When mounted on 1" square (650 mm²) PCB of FR-4 or G-10 material 4 oz. (140 μm] copper 40 °C/W For recommended footprint and soldering techniques refer to application note #AN-994

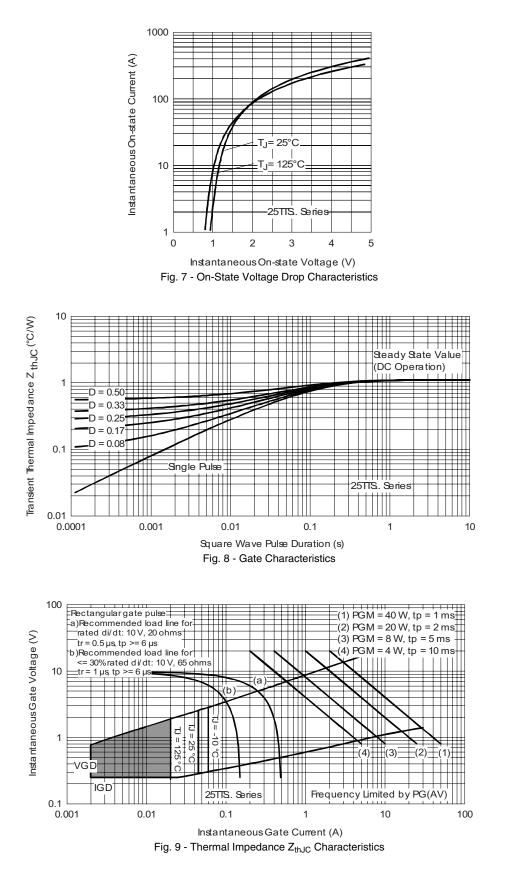
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ORDERING INFORMATION TABLE

Device code	25	т	т	s	16	S	TRL	-	
		2	3	4	5	6	7	8	
	1	- Cur	rent rati	ing (25 =	= 25 A)				
	2	- Circ	cuit conf	iguratio	n:				
		T =	Single	thyristor					
	3	- Pac	kage:						
	_	T =	TO-220	AC					
	4	- Тур	e of sili	con:			ſ		
	_			ecovery				08 =	800
	5			de x 100				12 = ´	
	6	- S=	TO-220) D ² PAK	(SMD-:	220) ve	rsion	16 = <i>′</i>	600
	7	• N	one = T	ube					
		• TI	RL = Ta	pe and r	eel (left	oriente	d)		
		• TI	RR = Ta	pe and	reel (rigl	nt orien	ted)		
	8	• • N	one = S	tandard	product	ion			
		• P	bF = Le	ad (Pb)-	free				

LINKS TO RELATED DOCUMENTS					
Dimensions http://www.vishay.com/doc?95046					
Part marking information	http://www.vishay.com/doc?95054				
Packaging information	http://www.vishay.com/doc?95032				



Vishay

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